V_{DSS}	100 V
I_D	8 A
$R_{DS(ON)}$	85 mΩ

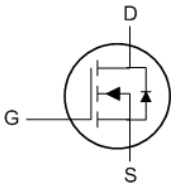
Description

The 8N10 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

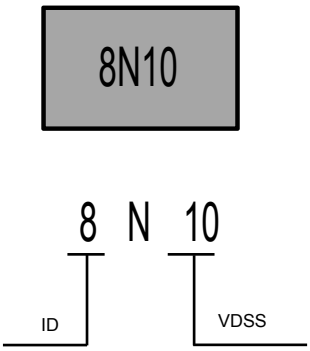
The 8N10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

Super Low Gate Charge
Green Device Available
Excellent Cdv/dt effect decline
Advanced high cell density Trench technology



Equivalent Circuit





SOT-89-3L top view

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	8	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	4.8	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	3	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	2.4	A
I_{DM}	Pulsed Drain Current[2]	20	A
EAS	Single Pulse Avalanche Energy[3]	6.1	mJ
I_{AS}	Avalanche Current	10	A
P_D@T_C=25℃	Total Power Dissipation[3]	30	W
P_D@T_A=25℃	Total Power Dissipation[3]	2	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	---	70	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	6.6	℃/W

Electrical Characteristics T_J=25℃ unless otherwise s ecified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=100V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}=±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}=10V, I_D=4A	-	85	110	mΩ
		V_{GS}=4.5V, I_D=2A	-	96	140	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=25V, V_{GS}=0V, f=1.0MHz	-	765	-	pF
C_{oss}	Output Capacitance		-	38	-	pF
C_{rss}	Reverse Transfer Capacitance		-	33	-	pF
Q_g	Total Gate Charge	V_{DS}=50V, I_D=2A, V_{GS}=10V	-	18	-	nC
Q_{gs}	Gate-Source Charge		-	2.5	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	4	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=50V, I_D=3A, R_G=1.8Ω, V_{GS}=10V	-	7.5	-	ns
t_r	Turn-on Rise Time		-	6	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	21	-	ns
t_f	Turn-off Fall Time		-	9	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	10	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	40	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=10A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F=3A, dI/dt=100A/μs	-	21	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	22	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25℃,V_{DD}=30V,V_G=10V,L=0.5mH,Rg=25Ω,I_{AS}=4A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

RATING AND CHARACTERISTIC CURVES

Figure1: Output Characteristics

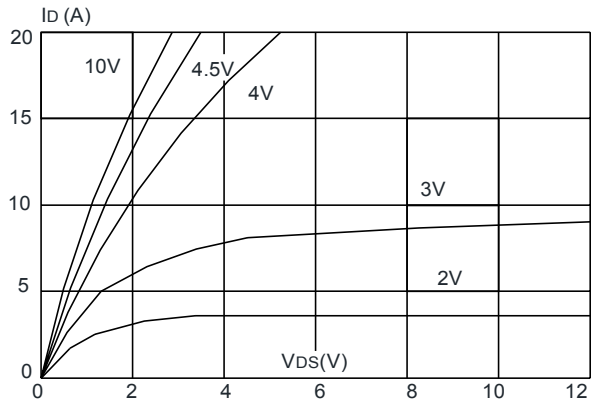


Figure 2: Typical Transfer Characteristics

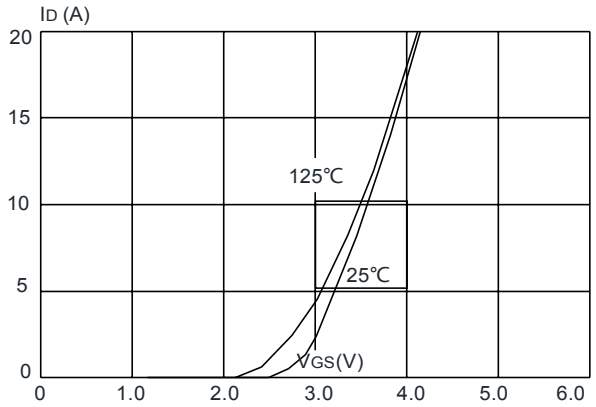


Figure 3: On-resistance vs. Drain Current

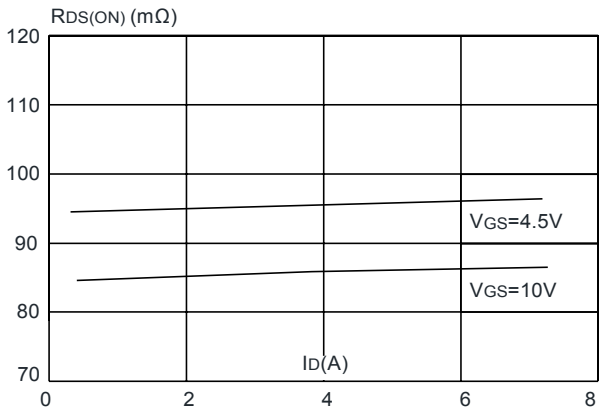


Figure 4 : Body Diode Characteristics

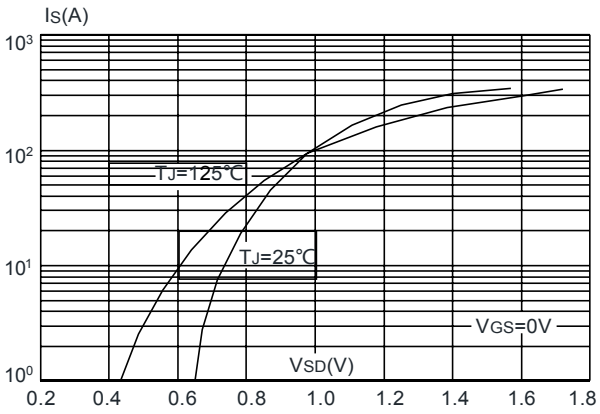


Figure 5: Gate Charge Characteristics

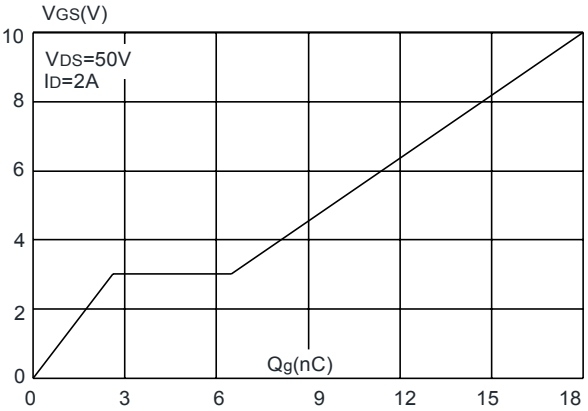
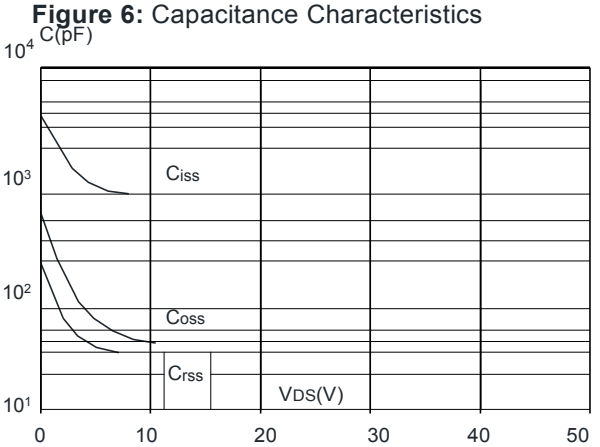


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

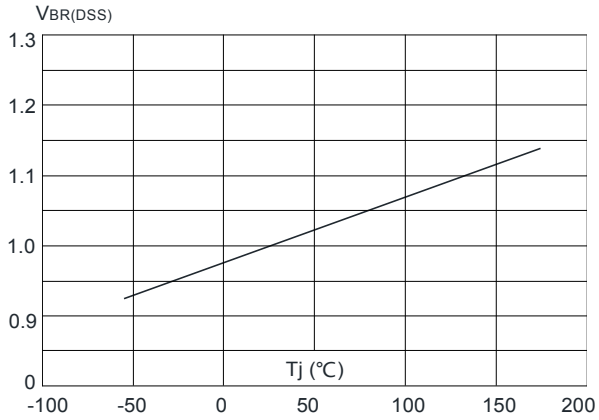


Figure 8: Normalized on Resistance vs. Junction Temperature

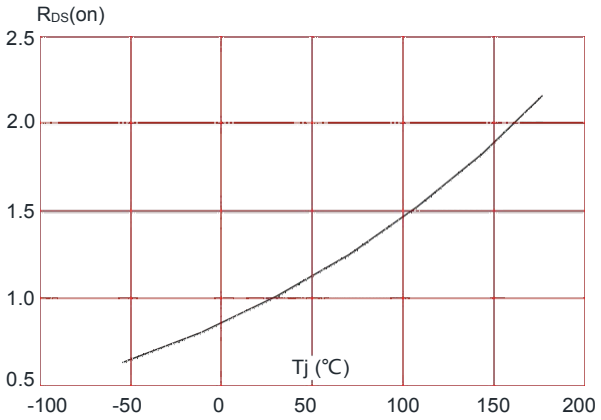


Figure 9: Maximum Safe Operating Area

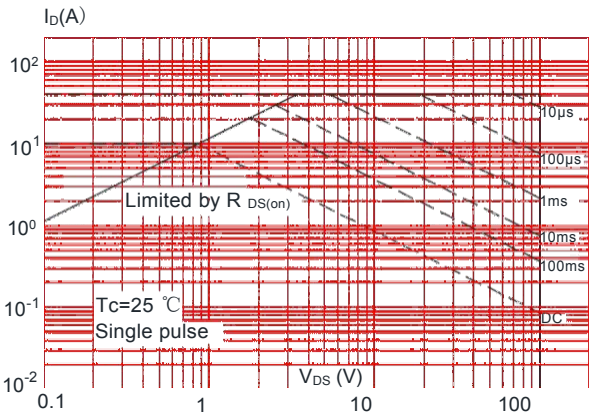


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

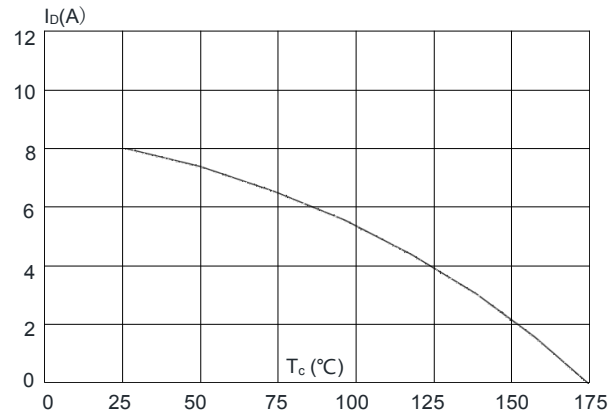
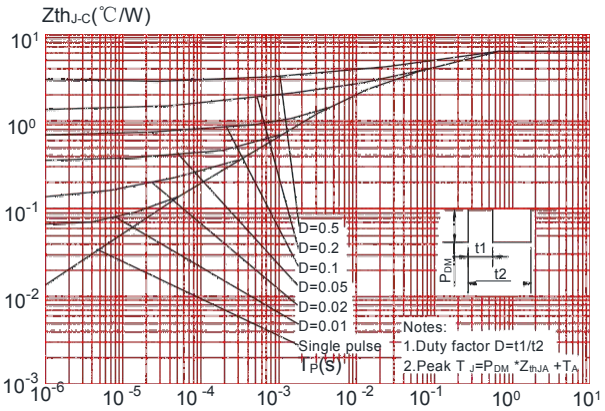


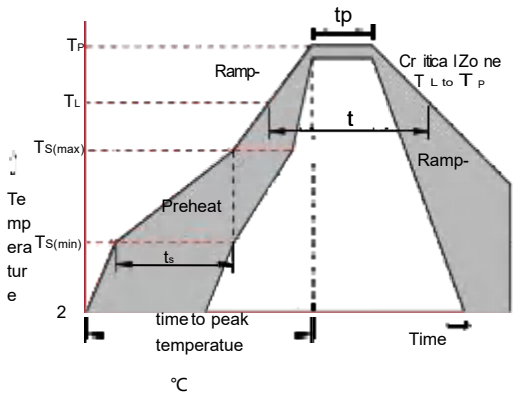
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Soldering parameters

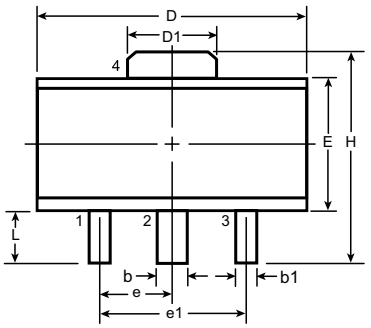
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

FIG5: Reflow condition

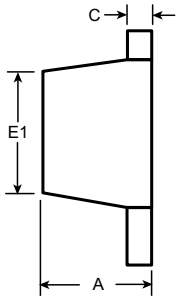


Package Dimensions & Suggested Pad Layout

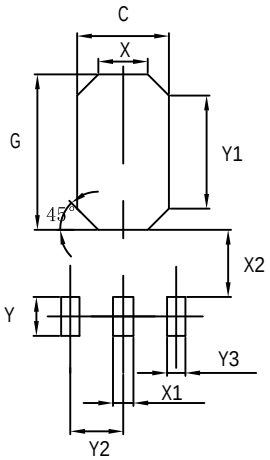
SOT89



Top View



Side View

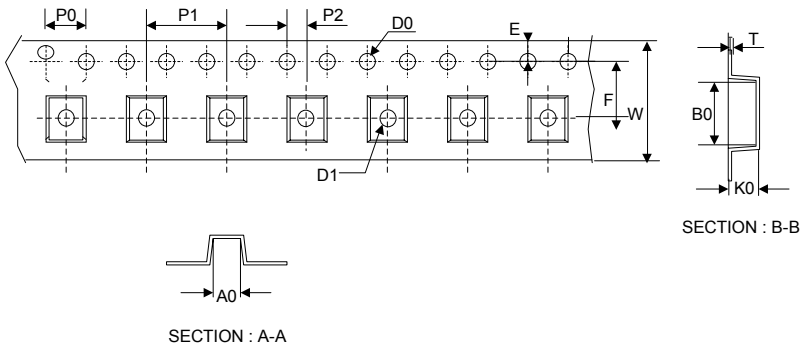


Symbol		A	b	b1	C	D	D1	E	E1	e	e1	H	L
Dimensions (mm)	MIN	1.40	0.44	0.36	0.3	4.40	1.50	2.29	2.00	1.50 BSC	3.00 BSC	3.94	0.89
	NOM	-	-	-	-	-	-	-	-			-	-
	MAX	1.60	0.56	0.48	0.5	4.60	1.75	2.60	2.29			4.25	1.20

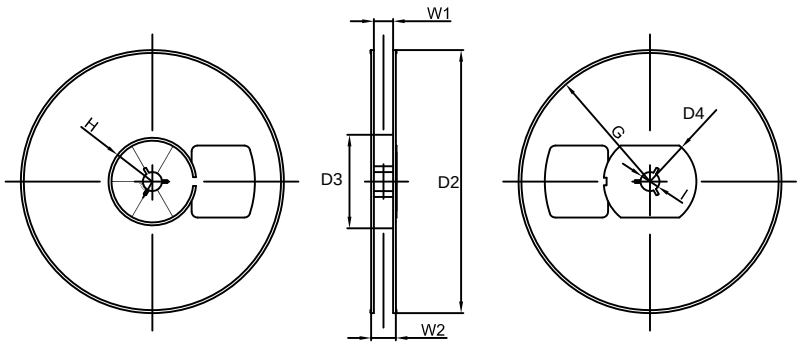
Dimensions	Value (in mm)
C	2.50
G	3.60
X	1.40
X1	0.90
X2	0.90
Y	1.40
Y1	2.60
Y2	1.50
Y3	0.90

Tape & rell specification

Tape



13” Reel



Symbol	Dimension (mm)
P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.60±0.20
D1	1.60±0.20
E	1.75±0.20
F	7.50±0.15
W	16.00±0.20
A0	6.30±0.20
B0	8.25±0.20
K0	2.60±0.20
T	0.23±0.10
D2	180.0±5.0
D3	60Min.
D4	R32.0±2.0
G	R86.5±2.0
H	R30.0±2.0
I	13.0±2.0
W1	13.20±2.0
W2	16.50±2.0
Quantity: 1000PCS	